Mingxing Wang

List of Publications by Year
in descending order

293 papers	7,202 citations	76196 40 h-index	82410 72 g-index
295 all docs	295 docs citations	295 times ranked	7883 citing authors

#	Article	IF	Citations
1	Growth of High Mobility InN Film on Gaâ€Polar GaN Substrate by Molecular Beam Epitaxy for Optoelectronic Device Applications. Advanced Materials Interfaces, 2023, 10, .	1.9	11
2	Excavating the Communication Performance in GaNâ€Based Green Microâ€LEDs: Modularâ€Architectured pâ€Type Region. Advanced Photonics Research, 2023, 4, .	1.7	2
3	Impact of Quantum Dots on III-Nitride Lasers: A Theoretical Calculation on Linewidth Enhancement Factors. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-7.	1.9	1
4	Lattice Polarity Manipulation of Quasiâ€vdW Epitaxial GaN Films on Graphene Through Interface Atomic Configuration. Advanced Materials, 2022, 34, e2106814.	11.1	19
5	High electron mobility in nearly-dislocation-free hexagonal InN. Applied Physics Express, 2022, 15, 011004.	1.1	3
6	Correlation between electrical properties and growth dynamics for Si-doped Al-rich AlGaN grown by metal-organic chemical vapor deposition. Superlattices and Microstructures, 2022, 163, 107141.	1.4	8
7	Effect of unintentional nitrogen incorporation on n-type doping of Î²-Ga₂O₃grown by molecular beam epitaxy. CrystEngComm, 2022, 24, 269-274.	1.3	6
8	Polarizationâ€Drivenâ€Orientation Selective Growth of Singleâ€Crystalline IIIâ€Nitride Semiconductors on Arbitrary Substrates. Advanced Functional Materials, 2022, 32, .	7.8	6
9	Low RF loss and low dislocation density of GaN grown on high-resistivity Si substrates. Applied Physics Express, 2022, 15, 031003.	1.1	3
10	Unidirectional Elimination of Hydrogen by a Giant Local Field Saves First- and Last-Mile Performances of Semiconductor Devices. Journal of Physical Chemistry Letters, 2022, 13, 2084-2093.	2.1	2
11	Sub-nanometer ultrathin epitaxy of AlGaN and its application in efficient doping. Light: Science and Applications, 2022, 11, 71.	7.7	22
12	Deepâ€Ultraviolet Microâ€LEDs Exhibiting High Output Power and High Modulation Bandwidth Simultaneously. Advanced Materials, 2022, 34, e2109765.	11.1	33
13	Infrared stimulated emission with an ultralow threshold from low-dislocation-density InN films grown on a vicinal GaN substrate. Fundamental Research, 2022, 2, 794-798.	1.6	2
14	Regulation of surface kinetics: rapid growth of n-AlGaN with high conductivity for deep-ultraviolet light emitters. CrystEngComm, 2022, 24, 4251-4255.	1.3	6
15	Atomicâ€Scale Investigation of the Latticeâ€Asymmetryâ€Driven Anisotropic Sublimation in GaN. Advanced Science, 2022, 9, .	5.6	5
16	Influence of intrinsic or extrinsic doping on charge state of carbon and its interaction with hydrogen in GaN. Applied Physics Letters, 2022, 120, .	1.5	2
17	Improvement in Modulation Bandwidth of Micro-LED Arrays Based on Low-Temperature-Interlayer Approach. IEEE Photonics Technology Letters, 2022, 34, 675-678.	1.3	1
18	Highâ€Efficiency Eâ€Beam Pumped Deepâ€Ultraviolet Surface Emitter Based on AlGaN Ultraâ€Thin Staggered Quantum Wells. Advanced Optical Materials, 2022, 10, .	3.6	5

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19	A scenario for high-temperature excitonic insulators. New Journal of Physics, 2022, 24, 083010.	1.2	1
20	Low-Resistive Ohmic Contacts in High-Electron-Mobility AlN/GaN Heterostructures by Suppressing the Oxygen Incorporation. ACS Applied Electronic Materials, 2022, 4, 3632-3639.	2.0	2
21	Colorâ€Tunable 3D InGaN/GaN Multiâ€Quantumâ€Well Lightâ€Emittingâ€Diode Based on Microfacet Emission and Programmable Driving Power Supply. Advanced Optical Materials, 2021, 9, .	3.6	14
22	Controlling Phaseâ€Coherent Electron Transport in IIIâ€Nitrides: Toward Room Temperature Negative Differential Resistance in AlGaN/GaN Double Barrier Structures. Advanced Functional Materials, 2021, 31, 2007216.	7.8	12
23	Secâ€Eliminating the SARSâ€CoVâ€2 by AlGaN Based High Power Deep Ultraviolet Light Source. Advanced Functional Materials, 2021, 31, 2008452.	7.8	67
24	Realization of high efficiency AlGaN-based multiple quantum wells grown on nano-patterned sapphire substrates. CrystEngComm, 2021, 23, 1201-1206.	1.3	14
25	Improved light extraction efficiency of AlGaN deep-ultraviolet light emitting diodes combining Ag-nanodots/Al reflective electrode with highly transparent p-type layer. Optics Express, 2021, 29, 2394.	1.7	15
26	High quality GaN-on-SiC with low thermal boundary resistance by employing an ultrathin AlGaN buffer layer. Applied Physics Letters, 2021, 118, .	1.5	12
27	Carrier Velocity Modulation by Asymmetrical Concave Quantum Barriers to Improve the Performance of AlGaN-Based Deep Ultraviolet Light Emitting Diodes. IEEE Photonics Journal, 2021, 13, 1-8.	1.0	4
28	Electrical Spin Injection into the 2D Electron Gas in AlN/GaN Heterostructures with Ultrathin AlN Tunnel Barrier. Advanced Functional Materials, 2021, 31, 2009771.	7.8	11
29	Interfacial symmetry breaking induced spin-orbit coupling in wurtzite GaN nanowires. Applied Physics Letters, 2021, 118, 122104.	1.5	2
30	Control of dislocations in heteroepitaxial AlN films by extrinsic supersaturated vacancies introduced through thermal desorption of heteroatoms. Applied Physics Letters, 2021, 118, .	1.5	11
31	Microstructure and dislocation evolution in composition gradient AlGaN grown by MOCVD. Superlattices and Microstructures, 2021, 152, 106842.	1.4	6
32	Structure and luminescence of a-plane GaN on r-plane sapphire substrate modified by Si implantation*. Chinese Physics B, 2021, 30, 056104.	0.7	1
33	High-mobility nâ^'-GaN drift layer grown on Si substrates. Applied Physics Letters, 2021, 118, .	1.5	5
34	Improved Ohmic contacts to plasma etched high Al fraction n-AlGaN by active surface pretreatment. Applied Physics Letters, 2021, 118, .	1.5	10
35	Demonstration of epitaxial growth of strain-relaxed GaN films on graphene/SiC substrates for long wavelength light-emitting diodes. Light: Science and Applications, 2021, 10, 117.	7.7	30
36	Reduced thermal boundary conductance in GaN-based electronic devices introduced by metal bonding layer. Nano Research, 2021, 14, 3616-3620.	5.8	7

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37	Monolayer-Scale GaN/AlN Multiple Quantum Wells for High Power e-Beam Pumped UV-Emitters in the 240â€“270 nm Spectral Range. Nanomaterials, 2021, 11, 2553.	1.9	10
38	Effect of a Lateral Overgrowth Process on the Strain Evolution of AlN Films Grown on a Nanopatterned Sapphire Substrate for Ultravioletâ€Ć Lightâ€Ėmitting Diode Applications. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100363.	1.2	4
39	Multi-channel AlGaN/GaN Schottky barrier diodes with a half through-hole. Materials Science in Semiconductor Processing, 2021, 133, 105934.	1.9	3
40	Material epitaxy of AlN thin films. Semiconductors and Semimetals, 2021, 107, 283-311.	0.4	1
41	Transferable room-temperature single-photon emitters in hexagonal boron nitride grown by molecular beam epitaxy. AIP Advances, 2021, 11, 115101.	0.6	1
42	Exciton-polariton properties of hexagonal BN-based microcavity and their potential applications in BEC and superconductivity. Physical Review B, 2021, 104, .	1.1	3
43	Ultra-thin AlGaN/GaN HFET with a high breakdown voltage on sapphire substrates. Applied Physics Letters, 2021, 119, .	1.5	5
44	Four-inch high quality crack-free AlN layer grown on a high-temperature annealed AlN template by MOCVD. Journal of Semiconductors, 2021, 42, 122804.	2.0	11
45	High quality AlN with uniform in-plane strain on nano-patterned AlN templates achieved by preset strain modulation. Japanese Journal of Applied Physics, 2021, 60, 120903.	0.8	4
46	Stress evolution in AlN growth on nano-patterned sapphire substrates. Applied Physics Express, 2020, 13, 015504.	1.1	13
47	Hexagonal BNâ€Assisted Epitaxy of Strain Released GaN Films for True Green Lightâ€Ėmitting Diodes. Advanced Science, 2020, 7, 2000917.	5.6	28
48	Three Subband Occupation of the Twoâ€Ďimensional Electron Gas in Ultrathin Barrier AlN/GaN Heterostructures. Advanced Functional Materials, 2020, 30, 2004450.	7.8	11
49	Influence of high-energy local orbitals and electron-phonon interactions on the band gaps and optical absorption spectra of hexagonal boron nitride. Physical Review B, 2020, 102, .	1.1	13
50	Direct evidence of hydrogen interaction with carbon: Câ€“H complex in semi-insulating GaN. Applied Physics Letters, 2020, 116, .	1.5	12
51	Nanopatterned sapphire substrate to enhance the efficiency of AlGaN-based UVC light source tube with CNT electron-beam. Journal of Materials Chemistry C, 2020, 8, 17336-17341.	2.7	7
52	High quality AlN film grown on a nano-concave-circle patterned Si substrate with an AlN seed layer. Applied Physics Letters, 2020, 117, .	1.5	13
53	Investigation of carrier compensation traps in nâ”-GaN drift layer by high-temperature deep-level transient spectroscopy. Applied Physics Letters, 2020, 117, .	1.5	7
54	Single-photon emission from isolated monolayer islands of InGaN. Light: Science and Applications, 2020, 9, 159.	7.7	20

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55	Cathodoluminescence nano-characterization of individual GaN/AlN quantum disks embedded in nanowires. Applied Physics Letters, 2020, 117, 133106.	1.5	3
56	Excitation and emission dynamics of a single photon emitting InGaN quantum dot in a photonic horn structure. Superlattices and Microstructures, 2020, 145, 106575.	1.4	2
57	Controlled bunching approach for achieving high efficiency active region in AlGaN-based deep ultraviolet light-emitting devices with dual-band emission. Applied Physics Letters, 2020, 116, .	1.5	16
58	Al diffusion at AlN/Si interface and its suppression through substrate nitridation. Applied Physics Letters, 2020, 116, .	1.5	23
59	III-nitrides based resonant tunneling diodes. Journal Physics D: Applied Physics, 2020, 53, 253002.	1.3	8
60	Grapheneâ€Assisted Epitaxy of Nitrogen Lattice Polarity GaN Films on Nonâ€Polar Sapphire Substrates for Green Light Emitting Diodes. Advanced Functional Materials, 2020, 30, 2001283.	7.8	41
61	3D-Ising critical behavior in antiperovskite-type ferromagneticlike Mn3GaN. Journal of Applied Physics, 2020, 127, 073903.	1.1	0
62	A GaN/AlN quantum cascade detector with a broad response from the mid-infrared (4.1â€‰Î¼m) to the visible (550â€‰nm) spectral range. Applied Physics Letters, 2020, 116, 171102.	1.5	13
63	Conductive transparent (InGa)2O3 film as host for rare earth Eu. AIP Advances, 2020, 10, 025024.	0.6	0
64	Thermally annealed wafer-scale h-BN films grown on sapphire substrate by molecular beam epitaxy. Applied Physics Letters, 2020, 116, .	1.5	16
65	Full-composition-graded InxGa1â^'xN films grown by molecular beam epitaxy. Applied Physics Letters, 2020, 117, 182101.	1.5	7
66	Vacancy-engineering-induced dislocation inclination in III-nitrides on Si substrates. Physical Review Materials, 2020, 4, .	0.9	20
67	Individually resolved luminescence from closely stacked GaN/AlN quantum wells. Photonics Research, 2020, 8, 610.	3.4	8
68	Observing near-infrared/ultraviolet responses within GaN/AlN superlattice for dual-band detection. , 2020, , .		0
69	Migration of carbon from Ga sites to N sites in GaN: a combined PAS and hybrid DFT study. Japanese Journal of Applied Physics, 2019, 58, 090901.	0.8	6
70	Single photon source based on an InGaN quantum dot in a site-controlled optical horn structure. Applied Physics Letters, 2019, 115, .	1.5	11
71	Intensive luminescence from a thick, indium-rich In0.7Ga0.3N film. Japanese Journal of Applied Physics, 2019, 58, 065503.	0.8	2
72	Epitaxy of Singleâ€Crystalline GaN Film on CMOSâ€Compatible Si(100) Substrate Buffered by Graphene. Advanced Functional Materials, 2019, 29, 1905056.	7.8	51

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73	Impact of Silicon Substrate with Low Resistivity on Vertical Leakage Current in AlGaN/GaN HEMTs. Applied Sciences (Switzerland), 2019, 9, 2373.	1.3	3
74	The sapphire substrate pretreatment effects on high-temperature annealed AlN templates in deep ultraviolet light emitting diodes. CrystEngComm, 2019, 21, 4632-4636.	1.3	8
75	Experimental Evidence of Large Bandgap Energy in Atomically Thin AlN. Advanced Functional Materials, 2019, 29, 1902608.	7.8	21
76	Planar anisotropic Shubnikov-de-Haas oscillations of two-dimensional electron gas in AlN/GaN heterostructure. Applied Physics Letters, 2019, 115, 152107.	1.5	5
77	Period size effect induced crystalline quality improvement of AlN on a nano-patterned sapphire substrate. Japanese Journal of Applied Physics, 2019, 58, 100912.	0.8	12
78	Puzzle of non-surface related 2D electron gas in n-InN epitaxial samples. Journal of Applied Physics, 2019, 126, 045705.	1.1	1
79	Realization of low dislocation density AlN on a small-coalescence-area nano-patterned sapphire substrate. CrystEngComm, 2019, 21, 2490-2494.	1.3	31
80	Dominant Influence of Interface Roughness Scattering on the Performance of GaN Terahertz Quantum Cascade Lasers. Nanoscale Research Letters, 2019, 14, 206.	3.1	11
81	Singleâ€photon emission from a further confined InGaN/GaN quantum disc via reverseâ€reaction growth. Quantum Engineering, 2019, 1, e20.	1.2	18
82	High performance of AlGaN deep-ultraviolet light emitting diodes due to improved vertical carrier transport by delta-accelerating quantum barriers. Applied Physics Letters, 2019, 114, .	1.5	30
83	Influence of intrinsic or extrinsic doping on lattice locations of carbon in semi-insulating GaN. Applied Physics Express, 2019, 12, 061002.	1.1	8
84	High-temperature annealing induced evolution of strain in AlN epitaxial films grown on sapphire substrates. Applied Physics Letters, 2019, 114, .	1.5	51
85	Deep Ultraviolet Light Source from Ultrathin GaN/AlN MQW Structures with Output Power Over 2 Watt. Advanced Optical Materials, 2019, 7, 1801763.	3.6	43
86	Repeatable asymmetric resonant tunneling in AlGaN/GaN double barrier structures grown on sapphire. Applied Physics Letters, 2019, 114, .	1.5	17
87	Determination of electron effective mass in InN by cyclotron resonance spectroscopy. Superlattices and Microstructures, 2019, 136, 106318.	1.4	1
88	Recombination processes in Mg doped wurtzite InN films with p- and n-type conductivity. AIP Advances, 2019, 9, 015114.	0.6	1
89	Î²-Ga₂O₃ thin film grown on sapphire substrate by plasma-assisted molecular beam epitaxy. Journal of Semiconductors, 2019, 40, 012802.	2.0	24
90	Repeatable Room Temperature Negative Differential Resistance in AlN/GaN Resonant Tunneling Diodes Grown on Sapphire. Advanced Electronic Materials, 2019, 5, 1800651.	2.6	32

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91	Greatly enhanced performance of AlGaN-based deep ultraviolet light emitting diodes by introducing a polarization modulated electron blocking layer. Optics Express, 2019, 27, A1458.	1.7	17
92	Determination of the transition point from electron accumulation to depletion at the surface of In_xGa_{1â^'}_xN films. Applied Physics Express, 2018, 11, 021001.	1.1	3
93	Electrical properties of surface and interface layers of the N- and In-polar undoped and Mg-doped InN layers grown by PA MBE. Applied Physics Letters, 2018, 112, 022104.	1.5	5
94	Vertical leakage induced current degradation and relevant traps with large lattice relaxation in AlGaN/GaN heterostructures on Si. Applied Physics Letters, 2018, 112, 032104.	1.5	8
95	High-electron-mobility InN epilayers grown on silicon substrate. Applied Physics Letters, 2018, 112, .	1.5	22
96	Effect of indium droplets on growth of InGaN film by molecular beam epitaxy. Superlattices and Microstructures, 2018, 113, 650-656.	1.4	10
97	Investigation of InGaN Layer Grown Under In-Rich Condition by Reflectance Difference Spectroscopy Microscope. Journal of Nanoscience and Nanotechnology, 2018, 18, 7468-7472.	0.9	3
98	Unambiguous Identification of Carbon Location on the N Site in Semi-insulating GaN. Physical Review Letters, 2018, 121, 145505.	2.9	45
99	Crystal quality evolution of AlN films via high-temperature annealing under ambient N₂ conditions. CrystEngComm, 2018, 20, 6613-6617.	1.3	28
100	Highâ€Mobility Twoâ€Dimensional Electron Gas at InGaN/InN Heterointerface Grown by Molecular Beam Epitaxy. Advanced Science, 2018, 5, 1800844.	5.6	18
101	Enhanced Hydrogen Detection Based on Mg-Doped InN Epilayer. Sensors, 2018, 18, 2065.	2.1	1
102	k-space imaging of anisotropic 2D electron gas in GaN/GaAlN high-electron-mobility transistor heterostructures. Nature Communications, 2018, 9, 2653.	5.8	43
103	Molecular beam epitaxy of single-crystalline aluminum film for low threshold ultraviolet plasmonic nanolasers. Applied Physics Letters, 2018, 112, .	1.5	15
104	Transition of dominant lattice sites of Mg in InN:Mg revealed by Raman scattering. Superlattices and Microstructures, 2018, 120, 533-539.	1.4	2
105	Elastically frustrated rehybridization: Origin of chemical order and compositional limits in InGaN quantum wells. Physical Review Materials, 2018, 2, .	0.9	36
106	Latticeâ€Symmetryâ€Driven Epitaxy of Hierarchical GaN Nanotripods. Advanced Functional Materials, 2017, 27, 1604854.	7.8	17
107	Nanoscale visualization of electronic properties of AlxGa1-xN/AlyGa1-yN multiple quantum-well heterostructure by spreading resistance microscopy. Journal of Applied Physics, 2017, 121, 014305.	1.1	4
108	Performance improvement of AlGaN-based deep-ultraviolet light-emitting diodes via asymmetric step-like AlGaN quantum wells. Superlattices and Microstructures, 2017, 104, 240-246.	1.4	20

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109	High quality AlN epilayers grown on nitrided sapphire by metal organic chemical vapor deposition. Scientific Reports, 2017, 7, 42747.	1.6	33
110	High quality and uniformity GaN grown on 150Âmm Si substrate using in-situ NH 3 pulse flow cleaning process. Superlattices and Microstructures, 2017, 104, 112-117.	1.4	5
111	Excitonic localization at macrostep edges in AlGaN/AlGaN multiple quantum wells. Superlattices and Microstructures, 2017, 104, 397-401.	1.4	19
112	Exciton emission of quasi-2D InGaN in GaN matrix grown by molecular beam epitaxy. Scientific Reports, 2017, 7, 46420.	1.6	14
113	Performance improvement of AlGaN-based deep-ultraviolet light-emitting diodes via Si-doping design of quantum barriers. Superlattices and Microstructures, 2017, 109, 687-692.	1.4	6
114	Enhanced transport properties in InAlGaN/AlN/GaN heterostructures on Si (111) substrates: The role of interface quality. Applied Physics Letters, 2017, 110, .	1.5	11
115	Hot electron assisted vertical leakage/breakdown in AlGaN/GaN heterostructures on Si substrates. Superlattices and Microstructures, 2017, 107, 240-245.	1.4	4
116	High-quality AlN epitaxy on sapphire substrates with sputtered buffer layers. Superlattices and Microstructures, 2017, 105, 34-38.	1.4	13
117	Influence of MBE growth modes and conditions on spontaneous formation of metallic In nanoparticles and electrical properties of InN matrix. Journal of Crystal Growth, 2017, 478, 216-219.	0.7	2
118	Local surface plasmon enhanced polarization and internal quantum efficiency of deep ultraviolet emissions from AlGaN-based quantum wells. Scientific Reports, 2017, 7, 2358.	1.6	18
119	Anomalous surface potential behavior observed in InN by photoassisted Kelvin probe force microscopy. Applied Physics Letters, 2017, 110, 222103.	1.5	3
120	Direct evidence of recombination between electrons in InGaN quantum discs and holes in p-type GaN. Optics Express, 2017, 25, 30664.	1.7	1
121	Identifying a doping type of semiconductor nanowires by photoassisted kelvin probe force microscopy as exemplified for GaN nanowires. Optical Materials Express, 2017, 7, 904.	1.6	24
122	Anisotropic strain relaxation and high quality AlGaN/GaN heterostructures on Si (110) substrates. Applied Physics Letters, 2017, 110, .	1.5	5
123	Reflectance difference spectroscopy microscope for circular defects on InN films. Optics Express, 2016, 24, 15059.	1.7	6
124	Photoconductivity in In_xGa_1-xN epilayers. Optical Materials Express, 2016, 6, 815.	1.6	7
125	Hot electron induced non-saturation current behavior at high electric field in InAlN/GaN heterostructures with ultrathin barrier. Scientific Reports, 2016, 6, 37415.	1.6	6
126	Edge Dislocations Triggered Surface Instability in Tensile Epitaxial Hexagonal Nitride Semiconductor. ACS Applied Materials & Interfaces, 2016, 8, 34108-34114.	4.0	7

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127	Mechanism of stress-driven composition evolution during hetero-epitaxy in a ternary AlGaN system. Scientific Reports, 2016, 6, 25124.	1.6	25
128	Spatial identification of traps in AlGaN/GaN heterostructures by the combination of lateral and vertical electrical stress measurements. Applied Physics Letters, 2016, 108, 042107.	1.5	5
129	Positive temperature coefficient of photovoltaic efficiency in solar cells based on InGaN/GaN MQWs. Applied Physics Letters, 2016, 109, .	1.5	17
130	Effect of stress on the Al composition evolution in AlGaN grown using metal organic vapor phase epitaxy. Applied Physics Express, 2016, 9, 051001.	1.1	5
131	Electrical properties of GaN-based heterostructures adopting InAlN/AlGaN bilayer barriers. Journal of Crystal Growth, 2016, 447, 1-4.	0.7	0
132	Growth of high quality n-Al 0.5 Ga 0.5 N thick films by MOCVD. Materials Letters, 2016, 176, 298-300.	1.3	7
133	Residual stress in AlN films grown on sapphire substrates by molecular beam epitaxy. Superlattices and Microstructures, 2016, 93, 27-31.	1.4	32
134	Origin of the wide band gap from 0.6 to 2.3 eV in photovoltaic material InN: quantum confinement from surface nanostructure. Journal of Materials Chemistry A, 2016, 4, 17412-17418.	5.2	6
135	Improvement of p -type conductivity in Al-rich AlGaN substituted by Mg Ga Î´ -doping (AlN) m /(GaN) n (m) Tj ETQq1 1 0.784314 rgBT	2.8	5
136	Physical origin of Davydov splitting and resonant Raman spectroscopy of Davydov components in multilayer<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">MoTe</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math>. Physical Review B, 2016, 93, .	1.1	93
137	Highâ€Outputâ€Power Ultraviolet Light Source from Quasiâ€2D GaN Quantum Structure. Advanced Materials, 2016, 28, 7978-7983.	11.1	72
138	High-quality AlN epitaxy on nano-patterned sapphire substrates prepared by nano-imprint lithography. Scientific Reports, 2016, 6, 35934.	1.6	110
139	Performance improvement of AlGaN-based deep-ultraviolet light-emitting diodes by inserting single spike barriers. Superlattices and Microstructures, 2016, 100, 941-946.	1.4	25
140	Growth of high quality and uniformity AlGaN/GaN heterostructures on Si substrates using a single AlGaN layer with low Al composition. Scientific Reports, 2016, 6, 23020.	1.6	52
141	Origin of Improved Optical Quality of Monolayer Molybdenum Disulfide Grown on Hexagonal Boron Nitride Substrate. Small, 2016, 12, 198-203.	5.2	22
142	Large-Scale Synthesis and Systematic Photoluminescence Properties of Monolayer MoS2 on Fused Silica. ACS Applied Materials & Interfaces, 2016, 8, 18570-18576.	4.0	26
143	High-resistance GaN epilayers with low dislocation density via growth mode modification. Journal of Crystal Growth, 2016, 450, 160-163.	0.7	6
144	Efficient silicon quantum dots light emitting diodes with an inverted device structure. Journal of Materials Chemistry C, 2016, 4, 673-677.	2.7	64

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145	Leakage Current Mechanism of InN-Based Metal-Insulator-Semiconductor Structures with Al2O3 as Dielectric Layers. Nanoscale Research Letters, 2016, 11, 21.	3.1	3
146	Lattice-Polarity-Driven Epitaxy of Hexagonal Semiconductor Nanowires. Nano Letters, 2016, 16, 1328-1334.	4.5	35
147	Elastic properties of indium nitrides grown on sapphire substrates determined by nano-indentation: In comparison with other nitrides. AIP Advances, 2015, 5, .	0.6	12
148	Mid-infrared Photoconductive Response in AlGaN/GaN Step Quantum Wells. Scientific Reports, 2015, 5, 14386.	1.6	10
149	Free and bound excitonic effects in Al0.5Ga0.5N/Al0.35Ga0.65N MQWs with different Si-doping levels in the well layers. Scientific Reports, 2015, 5, 13046.	1.6	20
150	Revealing of the transition from n- to p-type conduction of InN:Mg by photoconductivity effect measurement. Scientific Reports, 2015, 4, 4371.	1.6	25
151	Study on AlGaN P-I-N-I-N solar-blind avalanche photodiodes with Al0.45Ga0.55N multiplication layer. Electronic Materials Letters, 2015, 11, 1053-1058.	1.0	10
152	Epitaxial growth of AlN films on sapphire via a multilayer structure adopting a low- and high-temperature alternation technique. CrystEngComm, 2015, 17, 7496-7499.	1.3	53
153	Intersubband Transition in GaN/InGaN Multiple Quantum Wells. Scientific Reports, 2015, 5, 11485.	1.6	13
154	High mobility AlGaN/GaN heterostructures grown on Si substrates using a large lattice-mismatch induced stress control technology. Applied Physics Letters, 2015, 106, .	1.5	55
155	Tuning the graphene work function by uniaxial strain. Applied Physics Letters, 2015, 106, .	1.5	28
156	Correlation between switching to n-type conductivity and structural defects in highly Mg-doped InN. Applied Physics Letters, 2015, 106, 232102.	1.5	7
157	Hysteresis phenomena of the two dimensional electron gas density in lattice-matched InAlN/GaN heterostructures. Applied Physics Letters, 2015, 107, 052102.	1.5	5
158	Effects of light illumination on electron velocity of AlGaN/GaN heterostructures under high electric field. Applied Physics Letters, 2014, 105, 242104.	1.5	4
159	Epitaxy of InGaN random and digital alloys towards solar cells. , 2014, , .		0
160	Temperature-related exciton features on the Ga-/N-Faces of a free-standing HVPE GaN. Optical Materials Express, 2014, 4, 553.	1.6	0
161	Effect of injection current on the optical polarization of AlGaN-based ultraviolet light-emitting diodes. Optics Express, 2014, 22, 19589.	1.7	17
162	Effect of Mg doping on the structural and free-charge carrier properties of InN films. Journal of Applied Physics, 2014, 115, 163504.	1.1	16

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163	The discrepancies between theory and experiment in the optical emission of monolayer In(Ga)N quantum wells revisited by transmission electron microscopy. Applied Physics Letters, 2014, 104, .	1.5	48
164	Multi-bands photoconductive response in AlGaN/GaN multiple quantum wells. Applied Physics Letters, 2014, 104, 172108.	1.5	18
165	Formation of p-n-p junction with ionic liquid gate in graphene. Applied Physics Letters, 2014, 104, .	1.5	10
166	Electronic properties of polycrystalline graphene under large local strain. Applied Physics Letters, 2014, 104, .	1.5	17
167	Advantage of In- over N-polarity for disclosure of p-type conduction in InN:Mg. Journal of Applied Physics, 2014, 115, .	1.1	3
168	Epitaxial evolution on buried cracks in a strain-controlled AlN/GaN superlattice interlayer between AlGaN/GaN multiple quantum wells and a GaN template. Chinese Physics B, 2014, 23, 106106.	0.7	2
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